n-channel JFET *designed for . . .*

Siliconix

Performance Curves NRL
See Section 4

- **High Speed Commutators**
- **Choppers**

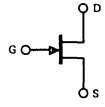
BENEFITS

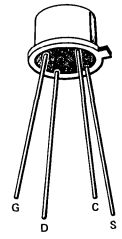
- Low Insertion Loss
  $r_{ds(on)} < 250\ \Omega$
- High Off-Isolation
  $I_{D(off)} < 0.1$ nA

*ABSOLUTE MAXIMUM RATINGS (25°C)

Gate-Drain or Gate-Source Voltage (Note 1) . . . −50 V
Gate Current . . . . . 10 mA
Total Device Dissipation at (or below) 25°C
Free-Air Temperature (Note 2) . . . . . 300 mW
Storage Temperature Range . . . . . −65 to +200°C
Lead Temperature
(1/16" from case for 10 seconds) . . . . . 300°C

TO-72
See Section 6





*ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

		Characteristic		Min	Max	Unit	Test Conditions	
1	STATIC	I_{GSS}	Gate Reverse Current		−0.1	nA	V_{GS} = −30 V, V_{DS} = 0	
2					−0.1	μA		150°C
3		BV_{GSS}	Gate-Source Breakdown Voltage	−50		V	I_G = −1 μA, V_{DS} = 0	
4		$I_{D(off)}$	Drain Cutoff Current		0.1	nA	V_{DS} = 15 V, V_{GS} = −8 V	
					0.1	μA		150°C
5	DYNAMIC	$r_{ds(on)}$	Drain-Source ON Resistance		250	Ω	V_{GS} = 0 V, I_D = 0	f = 1 kHz
6		C_{iss}	Common-Source Input Capacitance		6	pF	V_{DS} = 15 V, V_{GS} = 0	f = 1 MHz
7		C_{rss}	Common-Source Reverse Transfer Capacitance		3	pF	V_{GS} = −8 V, V_{DS} = 0	

*JEDEC registered data.

NRL

NOTES:
1. Due to symmetrical geometry, these units may be operated with source and drain leads interchanged.
2. Derate linearly to 175°C free-air temperature at rate of 2 mW/°C